

N-channel TrenchMOS logic level FET Rev. 02 — 26 April 2011

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

AEC Q101 compliant

Low conduction losses due to low on-state resistance

1.3 Applications

Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C	-	-	49	А
P _{tot}	total power dissipation		-	-	166	W
Static cha	aracteristics					
R_{DSon}	drain-source on-state	V_{GS} = 5 V; I _D = 25 A; T _j = 25 °C	-	18.5	28	mΩ
	resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	17	27	mΩ
Avalanch	e ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 30 \text{ A}; \text{V}_{\text{sup}} \leq 25 \text{ V}; \\ \text{R}_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 5 \text{ V}; \\ \text{T}_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	45	mJ



3.

BUK9628-100A

N-channel TrenchMOS logic level FET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT404 (D2PAK)

Ordering information

Table 3. Orde	ring information		
Type number	Package		
	Name	Description	Version
BUK9628-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

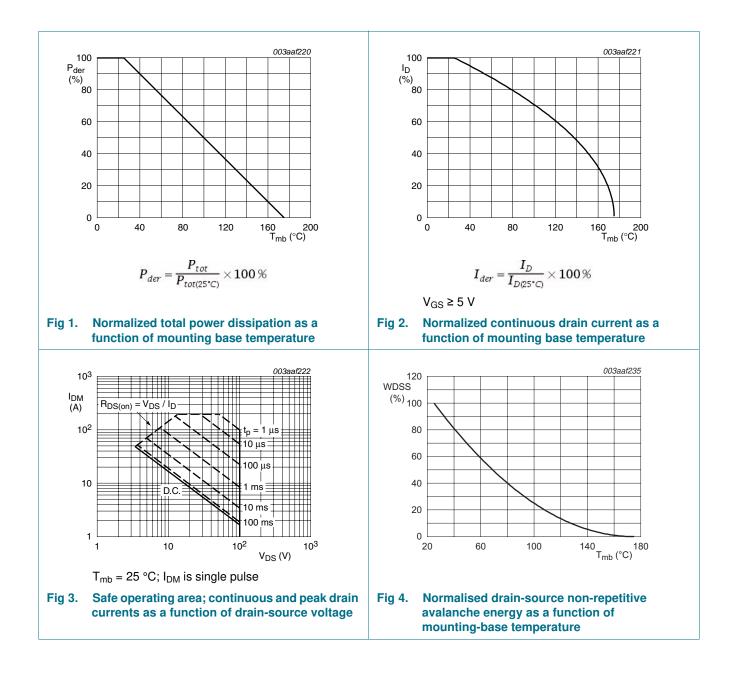
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-10	10	V
I _D	drain current	T _{mb} = 25 °C	-	49	А
		$T_{mb} = 100 \ ^{\circ}C$	-	34	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed	-	195	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	166	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V _{GSM}	peak gate-source voltage	pulsed; t _p ≤ 50 μs	-15	15	V
Source-dra	ain diode				
ls	source current	T _{mb} = 25 °C	-	49	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	195	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} I_{D} = 30 \; A; \; V_{sup} \leq 25 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 5 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array} $	-	45	mJ

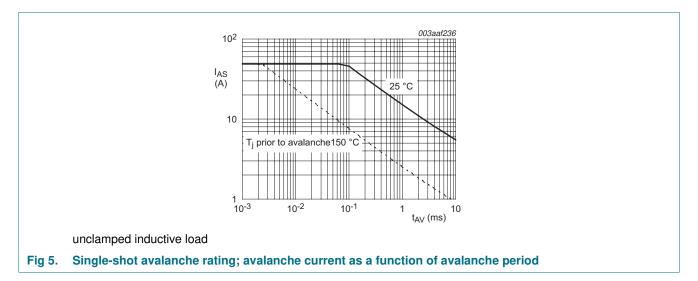
BUK9628-100A

N-channel TrenchMOS logic level FET



BUK9628-100A

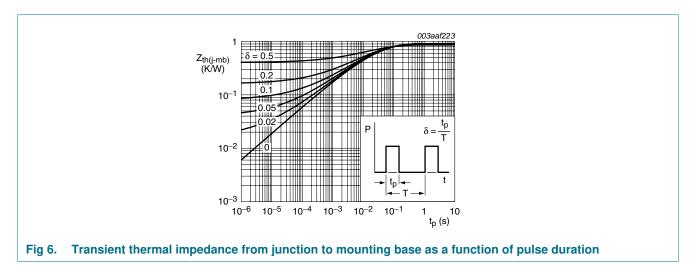
N-channel TrenchMOS logic level FET



5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	-	0.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; FR4 board	-	50	-	K/W



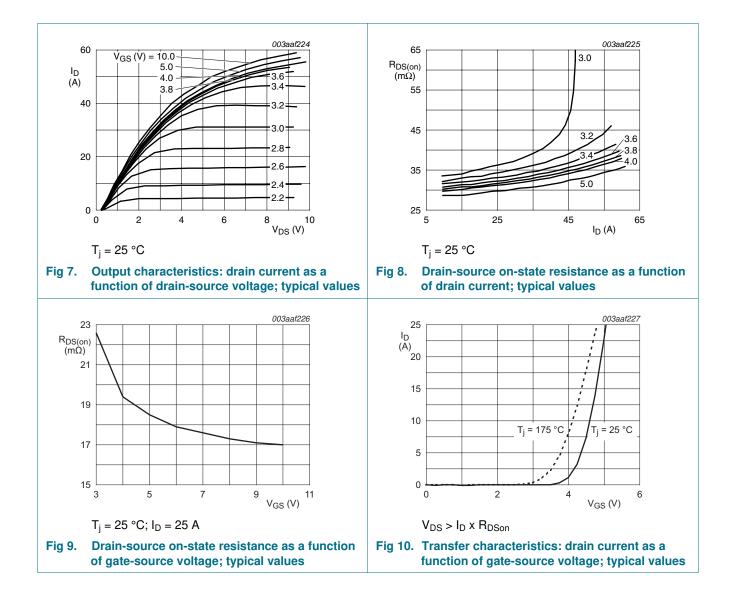
N-channel TrenchMOS logic level FET

6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.3	V
DSS	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
GSS	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 25 \text{ °C}$	-	18.5	28	mΩ
	resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C	-	-	70	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	17	27	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	18.8	31	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	3220	4293	pF
C _{oss}	output capacitance	T _j = 25 °C	-	315	378	pF
C _{rss}	reverse transfer capacitance		-	187	256	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	11	16	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	58	87	ns
t _{d(off)}	turn-off delay time		-	250	350	ns
t _f	fall time		-	106	148	ns
L _D	internal drain inductance	measured from drain lead 6 mm from package to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	4.5	-	nH
		measured from upper edge of drain tab to centre of die ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
-s	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.85	1.2	V
		$I_{S} = 49 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	1.1	-	V
t _{rr}	reverse recovery time	$I_{S} = 49 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	63	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	0.22	-	μC

BUK9628-100A

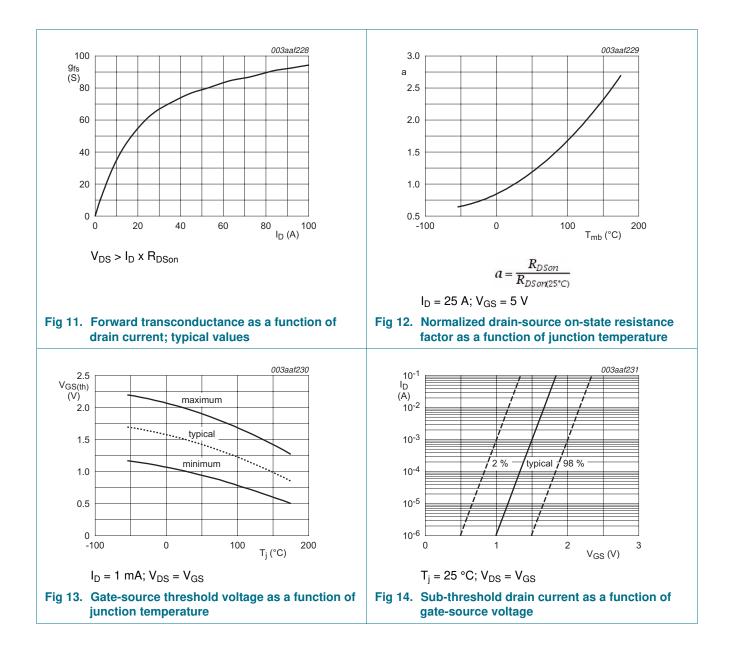
N-channel TrenchMOS logic level FET



BUK9628-100A

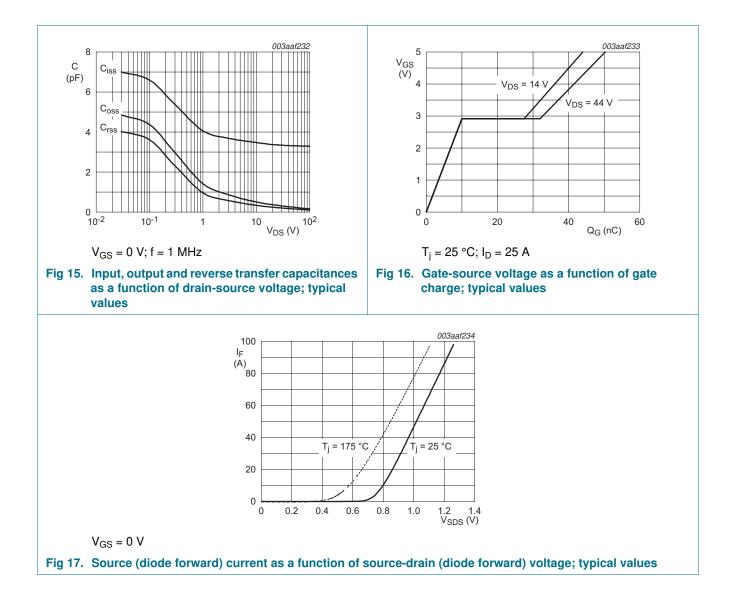
BUK9628-100A

N-channel TrenchMOS logic level FET



BUK9628-100A

N-channel TrenchMOS logic level FET



N-channel TrenchMOS logic level FET

Package outline 7.

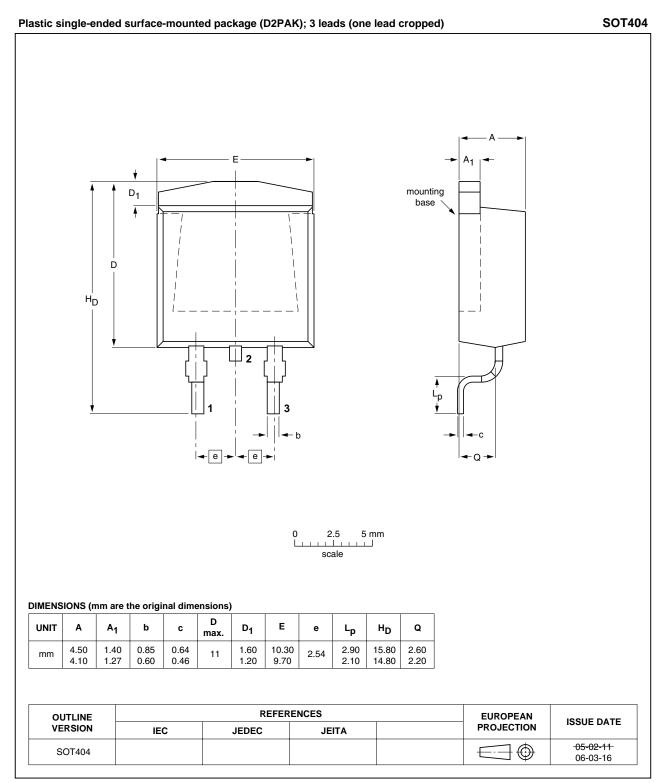


Fig 18. Package outline SOT404 (D2PAK)

BUK9628-100A

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N-channel TrenchMOS logic level FET

8. Revision history

Table 7.	Revision history				
Document	ID	Release date	Data sheet status	Change notice	Supersedes
BUK9628-1	00A v.2	20110426	Product data sheet	-	BUK9528_9628-100A v.1
Modifications:		guidelines of l Legal texts has 	this data sheet has been NXP Semiconductors. ave been adapted to the r BUK9628-100A separate	new company name	
BUK9528_	9628-100A v.1	20000301	Product specification	-	-

N-channel TrenchMOS logic level FET

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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BUK9628-100A

Rev. 02 — 26 April 2011

N-channel TrenchMOS logic level FET

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N-channel TrenchMOS logic level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12